STW29NK50Z

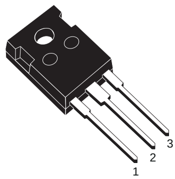
N-CHANNEL 500 V - 0.105Ω - 31A TO-247
Zener-Protected SuperMESH™ MOSFET

Table 1: General Features

TYPE	V_{DSS}	$R_{DS(on)}$	I_D	P_W
STW29NK50Z	500 V	< 0.13 Ω	31 A	350 W

- TYPICAL R_{DS}(on) = 0.105 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

Figure 1: Package



TO-247

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding application. Such series complements ST full range of high vltage MOS-FETs including revolutionary MDmesh™ products.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES
- WELDING MACHINES
- LIGHTING

Figure 2: Internal Schematic Diagram

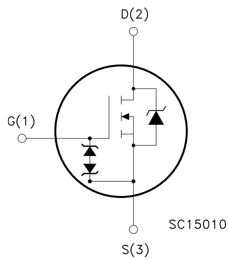


Table 2: Order Codes

PART NUMBER	MARKING	PACKAGE	PACKAGING
STW29NK50Z	W29NK50Z	TO-247	TUBE

Rev. 1

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 KΩ)	500	V
V_{GS}	Gate- source Voltage	± 30	V
I_D	Drain Current (continuous) at T_C = 25°C	31	A
I_D	Drain Current (continuous) at T_C = 100°C	19.5	A
I_{DM} (*)	Drain Current (pulsed)	124	A
P_{TOT}	Total Dissipation at T_C = 25°C	350	W
	Derating Factor	2.77	W/°C
$V_{ESD(G-S)}$	Gate source ESD (HBM-C = 100pF, R = 1.5 KΩ)	6000	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T_{stg} T_j	Storage Temperature Operating Junction Temperature	-55 to 150	°C

(*) Pulse width limited by safe operating area
(1) $I_{SD} \leq$ 31 A, di/dt ≤ 200 A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$

Table 4: Thermal Data

Rthj-case	Thermal Resistance Junction-case Max	0.36	°C/W
Rthj-amb T_l	Thermal Resistance Junction-ambient Max Maximum Lead Temperature For Soldering Purpose	50 300	°C/W °C

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	31	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	550	mJ

Table 6: Gate-Source Zener Diode

Symbol	Parameter	Test Condition	Min.	Typ.	Max	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs= ± 1mA (Open Drain)	30			A

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

TABLE 7: ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

On /Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	500			S
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125°C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 150 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 15.5 A		0.105	0.13	Ω

Table 8: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} = 15 V, I_D = 15.5 A		24		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0		6110 697 166		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Turn-off-Delay Time Fall Time	V_{DD} = 250 V, I_D = 15 A, R_G = 4.7 Ω, V_{GS} = 10 V (Resistive Load see Figure 17)		44.5 41 129 33		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 400 V, I_D = 30 A, V_{GS} = 10 V		190 35.5 111	266	nC nC nC

Table 9: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				31 124	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 31 A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 30 A, di/dt = 100 A/µs V_{DD} = 44.8V, T_j = 25°C (see test circuit Figure 5)		436 6.1 28		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 30 A, di/dt = 100 A/µs V_{DD} = 44.8V, T_j = 150°C (see test circuit Figure 5)		500 7.5 30		ns µC A

(1) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
(2) Pulse width limited by safe operating area.

Figure 3: Safe Operating Area

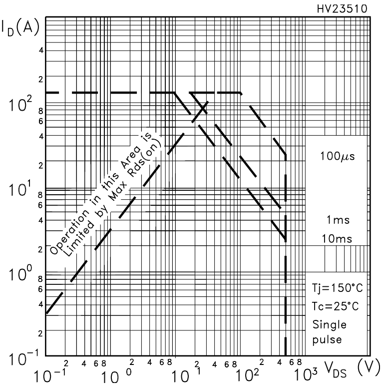


Figure 6: Thermal Impedance

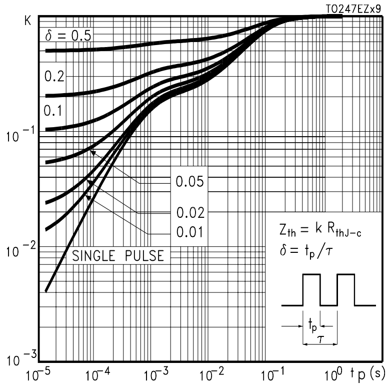


Figure 4: Output Characteristics

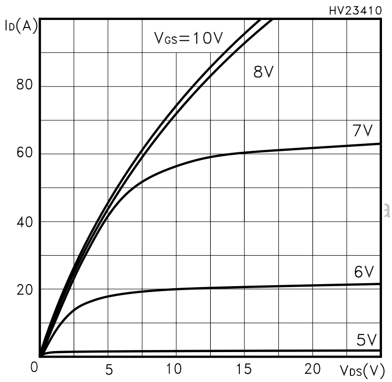


Figure 7: Transfer Characteristics

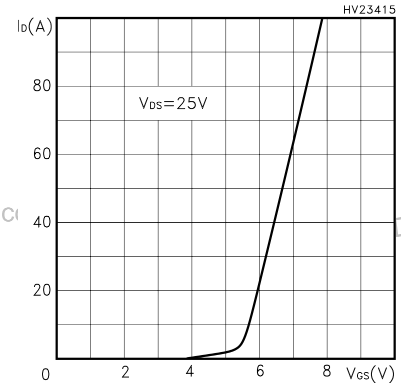


Figure 5: Transconductance

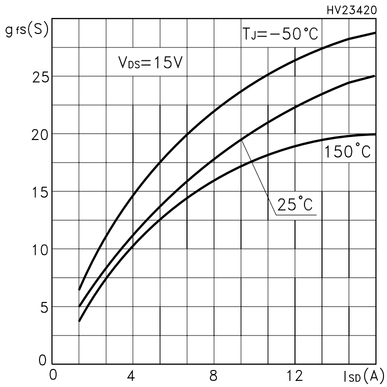


Figure 8: Static Drain-source On Resistance

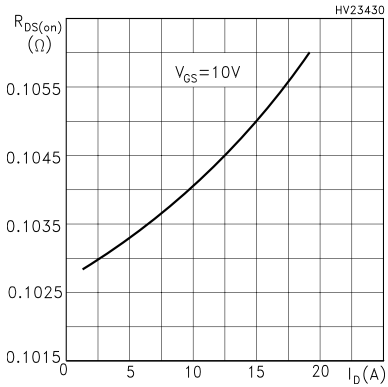


Figure 9: Gate Charge vs Gate-source Voltage

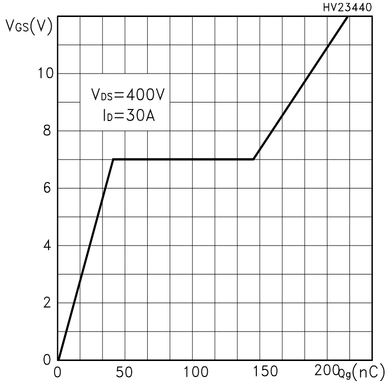


Figure 12: Capacitance Variations

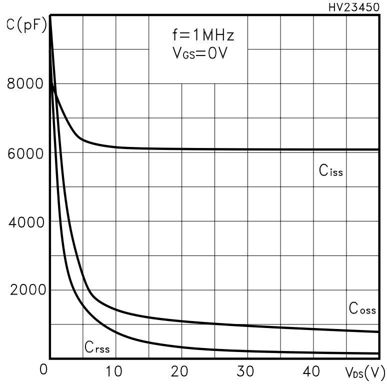


Figure 10: Normalized Gate Thereshold Voltage vs Temperature

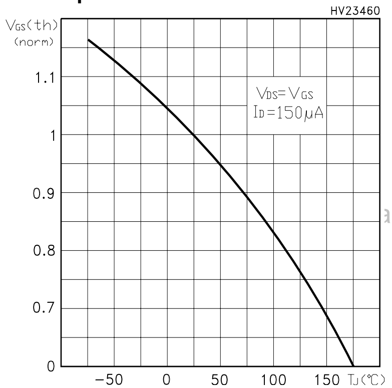


Figure 13: Normalized On Resistance vs Temperature

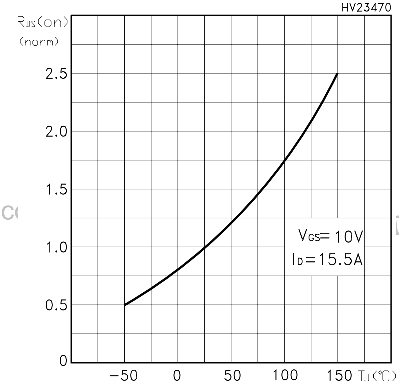


Figure 11: Dource-Drain Diode Forward Characteristics

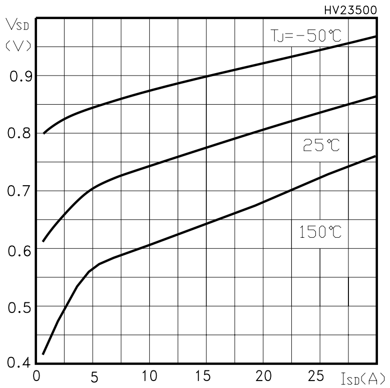


Figure 14: Normalized BV_{DSS} vs Temperature

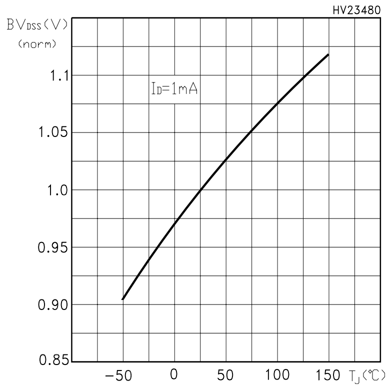


Figure 15: Maximum Avalanche Energy vs Temperature

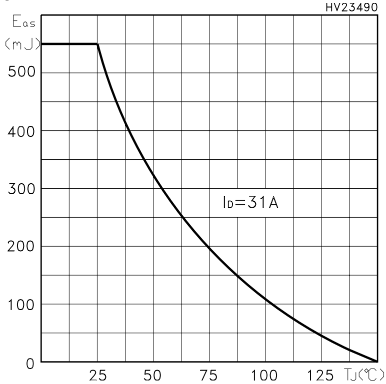


Figure 16: Unclamped Inductive Load Test Circuit

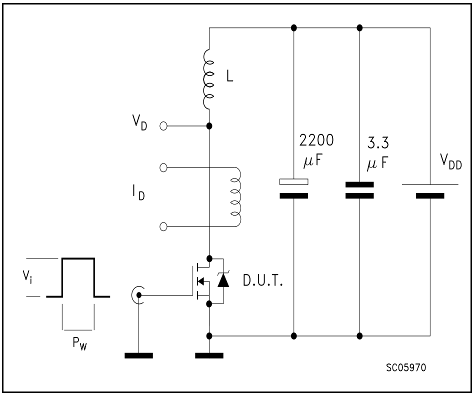


Figure 17: Switching Times Test Circuit For Resistive Load

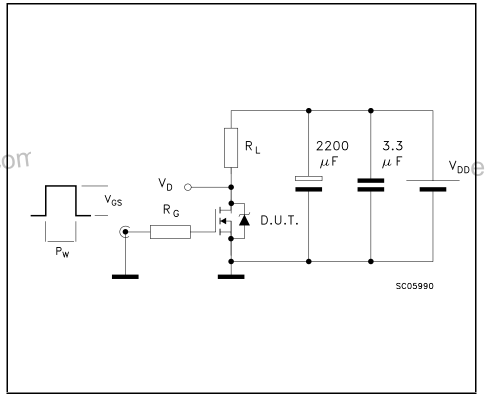


Figure 18: Test Circuit For Inductive Load Switching and Diode Recovery Times

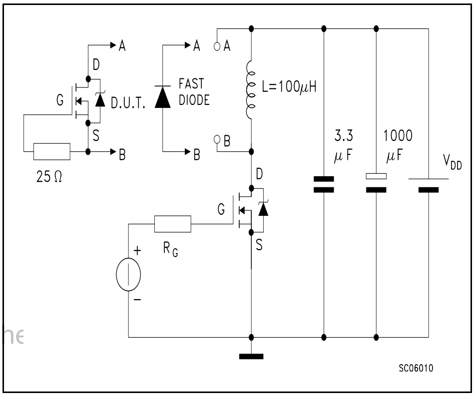


Figure 19: Unclamped Inductive Wafeform

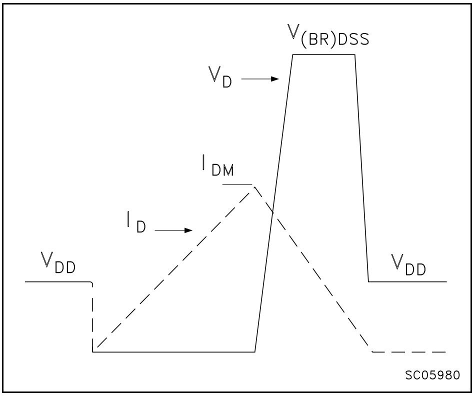
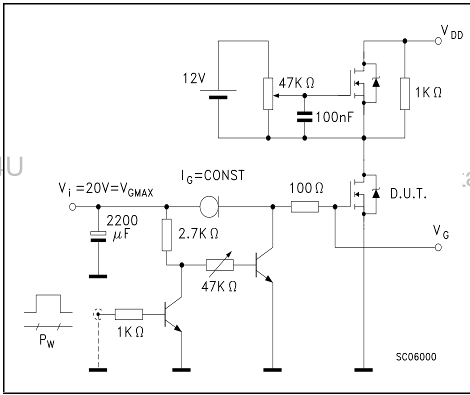


Figure 20: Gate Charge Test Circuit



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

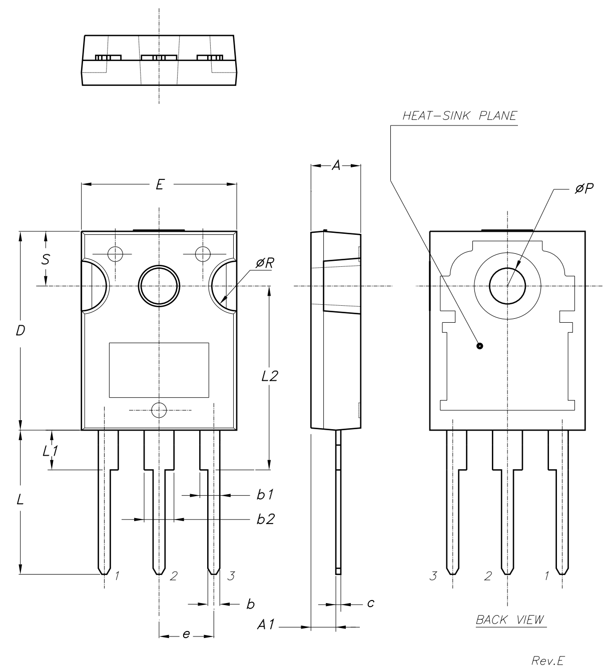


Table 10: Revision History

Date	Revision	Description of Changes
19-Oct-2004	1	First Release.

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